

## **isc Silicon NPN Power Transistor**

# **BUS48AP**

#### **DESCRIPTION**

- · High Voltage Capability
- · High Current Capability
- · Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

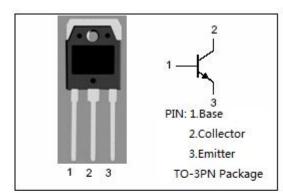
Designed for high-voltage, high-speed, power switching in inductive circuits where fall time is critical. They are particulary suited for line-operated swtchmode applications

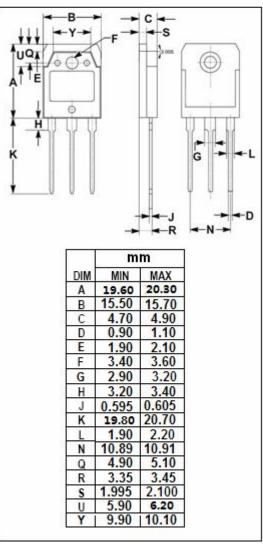
### Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CEV</sub>	Collector-Emitter Voltage	1000	V
V <sub>CEO</sub>	Collector-Emitter Voltage	450	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
Ic	Collector Current-Continuous	15	Α
Ісм	Collector Current-Peak	30	Α
I <sub>B</sub>	Base Current-Continuous	5	Α
I <sub>BM</sub>	Base Current-peak	20	Α
Pc	Collector Power Dissipation @T <sub>C</sub> =25°C	150	W
Tj	Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature Range	-65~150	$^{\circ}$

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	1.0	°C/W







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0;	450		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	7		V
V <sub>CE</sub> (sat)-1	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 8A; I <sub>B</sub> = 1.6A I <sub>C</sub> = 8A; I <sub>B</sub> = 1.6A;T <sub>C</sub> = 100°C		1.5 2.0	V
V <sub>CE</sub> (sat)-2	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 12A; I <sub>B</sub> = 2.4A		5.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 8A; I <sub>B</sub> = 1.6A I <sub>C</sub> = 8A; I <sub>B</sub> = 1.6A;T <sub>C</sub> = 100°C		1.6 1.6	V
I <sub>CBO</sub>	Collector Base Cutoff Current	V <sub>CE</sub> =1000V; I <sub>E</sub> = 0 V <sub>CE</sub> =1000V; I <sub>E</sub> = 0;T <sub>C</sub> =125°C		0.2 2.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0		0.1	mA
h <sub>FE</sub>	DC Current Gain	Ic= 8A; VcE= 5V	8		



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